# LVDT signal conditioner

## NE/SA/SE5521

#### DESCRIPTION

The NE/SA/SE5521 is a signal conditioning circuit for use with Linear Variable Differential Transformers (LVDTs) and Rotary Variable Differential Transformers (RVDTs). The chip includes a low distortion, amplitude-stable sine wave oscillator with programmable frequency to drive the primary of the LVDT/RVDT, a synchronous demodulator to convert the LVDT/RVDT output amplitude and phase to position information, and an output amplifier to provide amplification and filtering of the demodulated signal.

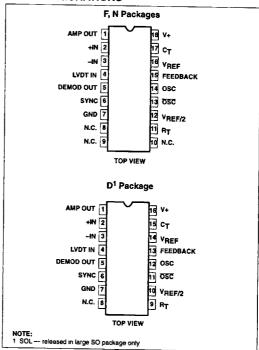
#### **FEATURES**

- Low distortion
- Single supply 5V to 20V, or dual supply ±2.5V to ±10V
- Oscillator frequency 1kHz to 20kHz
- Capable of ratiometric operation
- Low power consumption (182mV typ)

#### **APPLICATIONS**

- LVDT signal conditioning
- RVDT signal conditioning
- LPDT signal conditioning
- Bridge circuits

## **PIN CONFIGURATIONS**



#### **ORDERING INFORMATION**

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE	DWG#
18-Pin Plastic Dual In-Line Package (DIP)	0 to +70°C	NE5521N	0407A
16-Pin Small Outline Large (SOL) Package	0 to +70°C	NE5521D	0171B
18-Pin Plastic Dual In-Line Package (DIP)	-40 to +85°C	SA5521N	0407A
18-Pin Ceramic Dual In-Line Package (CERDIP)	-55 to +125°C	SE5521F	0583A
16-Pin Ceramic Dual In-Line Package (CERDIP)	-40 to +85°C	SA5521D	0583A

## **ABSOLUTE MAXIMUM RATINGS**

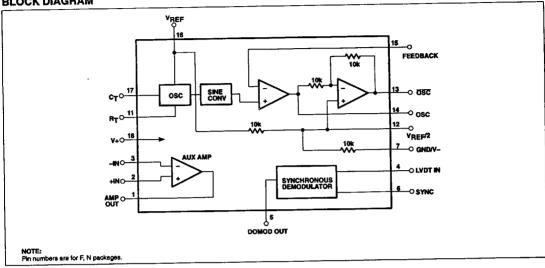
SYMBOL	PARAMETER	RATING	UNIT
/cc	Supply voltage	+20	
	Split supply voltage	±10	<del></del>
T <sub>A</sub>	Operating temperature range NE5521 SA5521 SE5521	0 to 70 -40 to +85 -55 to +125	ပံ့
STG	Storage temperature range	-65 to +125	°C
P <sub>D</sub>	Power dissipation <sup>1</sup>	910	mW

NOTES:

1. For derating, see typical power dissipation versus load curves (Figure 1).

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#### **BLOCK DIAGRAM**



# PIN DEFINITIONS FOR D, F AND N PACKAGES

PIN NO.		SYMBOL	DEFINITION					
D	F, N	STMBUL						
1	1	Amp Out	Auxiliary Amplifier Out.					
2	2	+IN	Auxiliary Amplifier non-inverting input.					
3	3	⊣N	Auxiliary Amplifier inverting input.					
4	4	LVDT IN	input to Synchronous Demodulator from the LVDT/RVDT secondary.					
5	5	DEMOD OUT	pulsating DC output from the Synchronous Demodulator output. This voltage should be filtered before use.					
6	6	SYNC	Synchronizing input for the Synchronizing Demodulator. This input should be connected to the OSC or OSC output. Sync is referenced to VREF/2.					
7	7	GND	Device return. Should be connected to system ground or to the negative supply.					
8	8	NC	No internal connection.					
_	9	NC	No internal connection.					
	10	NC	No internal connection.					
9	11	RT	A temperature stable 18kΩ resistor should be connected between this pin and Pin 7.					
10	12	V <sub>REF</sub> /2	A high impedance source of one half the potential applied to V <sub>REF</sub> . The LVDT/RVDT secondary return should be to this point. A bypass capacitor with low impedance at the oscillator frequency should also be connected between this pin and ground.					
11	13	OSC	Oscillator sine wave output that is 180° out of phase with the OSC signal. The LVDT/RVDT primary is usually connected between OSC and OSC pins.					
12	14	OSC	Oscillator sine wave output. The LVDT/RVDT primaries are usually connected between OSC and OSC					
13	15	FEEDBACK	Usually connected to the OSC output for unity gain, a resistor between this pin and OSC, and one between this pin and ground can provide for a change in the oscillator output pin amplitudes.					
14	16	V <sub>REF</sub>	Reference voltage input for the oscillator and sine converter. This voltage MUST be stable and must not acceed at supply voltage.					
15	17	Ст	Oscillator frequency-determining capacitor. The capacitor connected between this pin and ground should be a temperature-stable type.					
16	18	+٧	Positive supply connection.					

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## DC ELECTRICAL CHARACTERISTICS

 $V_{+} = V_{REF} = 10V$ ,  $T_{A} = 0$  to 70°C for NE5521,  $T_{A} = -55$  to +125°C for SE5521,  $T_{A} = -40$  to 85°C for SA5521, Frequency = 1kHz, unless otherwise noted.

SYMBOL	PARAMETER	TEST CONDITIONS		NE5521			SA/SE5521		
			Min	Тур	Max	Min	Тур	Max	UNIT
v <sub>cc</sub>	Supply current			12.9	20		12.9	18	mA
IREF	Reference current			5.3	8		5.3	8	mA
V <sub>REF</sub>	Reference voltage range		5		V+	5		V+	V
PD	Power dissipation			182	280		182	260	mW
Oscillato	r Section					Ь			
	Oscillator output	$R_L = 10k\Omega$	V <sub>REF</sub>				V <sub>REF</sub>		V <sub>RMS</sub>
THD	Sine wave distortion	No load	1 0.0	1.5			1.5		%
	Initial amplitude error	T <sub>A</sub> = 25°C		0.4	±3		0.4	±3	%
	Tempco of amplitude			0.005	0.01		0.005	0.01	%/°C
	Init. accuracy of oscillator freq.	T <sub>A</sub> = 25°C		±0.9	±5	<del></del>	±0.9	±5	% %
	Temperature coeff. of frequency <sup>1</sup>		+	0.05	-		0.05	13	%/°C
	Voltage coeff. of frequency		+	2.5		-	3.3		
	Min OSC (OSC) Load <sup>2</sup>		300	170		300	170		%/V(V <sub>REF</sub>
Demodul	ator Section		1 000	170		300	170		Ω
€r	Linearity error	5V <sub>P-P</sub> input	T	±0.05	±0.1		±0.05	±0.1	%FS
	Maximum demodulator input			V <sub>REF</sub>			V <sub>REF</sub>		V <sub>P-P</sub>
Vos	Demodulator offset voltage			±1.4	±5		2 ±1.4	±5	mV
TCV <sub>OS</sub>	Demodulator offset voltage drift			5	25		5	25	μV/ <sup>5</sup> C
BIAS	Demodulator input current		-600	-234		-500	-234	20	nA
	V <sub>R/2</sub> accuracy		1 111	±0.1	±1	- 500	±0.1	±1	%
Auxiliary	Output Amplifier				4.		20.1	Τ.	76
Vos	Input offset voltage		1	±0.5	±5		±0.5	±5	mV
IBIAS	Input bias current		-600	-210		-500	-210		nA
los	Input offset current		1	10	50		10	50	
Av	Gain		100	385		100	385	30	nA V/m/
SR	Slew rate		1.00	1.3		100	1.3		V/mV
GBW	Unity gain bandwidth product	A <sub>V</sub> = 1	+	1.6			1.6		V/μs
	Output voltage swing	$R_L = 10k\Omega$	7	8.2	-	7	$\overline{}$		MHz
	Output short circuit current to ground or to VCC	T <sub>A</sub> = 25°C		42	100		8.2 42	100	MA.

<sup>1.</sup> This is temperature coefficient of frequency for the device only. It is assumed that C<sub>T</sub> and R<sub>T</sub> are fixed in value and C<sub>T</sub> leakage is fixed over the operating temperature range.

2. Minimum load impedance for which distortion is guaranteed to be less than 5%.

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#### **DEFINITION OF TERMS**

Oscillator Output	RMS value of the AC voltage at the oscillator output pin. This output is referenced to V <sub>REF/2</sub> and is a function of V <sub>REF</sub>
Sine Wave Distortion	The Total Harmonic Distortion (THD) of the oscillator output with no load. This is not a critical specification in LVDT/RVDT systems. This figure could be 15% or more without affecting system performance.
Initial Amplitude Error	A measure of the interchangeability of NE/SA/SE5521 parts, not a characteristic of any one part. It is the degree to which the oscillator output of a number of NE/SA/SE5521 samples will vary from the median of that sample.
Initial Accuracy of Oscillator Frequency	Another measure of the interchangeability of individual NE/SA/SE5521 parts. This is the degree to which the oscillator frequency of a number of NE/SA/SE5521 samples will vary from the median of that sample with a given timing capacitor.
Tempco of Oscillator Amplitude	A measure of how the oscillator amplitude varies with ambient temperature as that temperature deviates from a 25°C ambient.
Tempco of Oscillator Frequency	A measure of how the oscillator frequency varies with ambient temperature as that temperature deviates from a 25°C ambient.
Voltage Coefficient of Oscillator Frequency	The degree to which the oscillator frequency will vary as the reference voltage (V <sub>REF</sub> ) deviates from +10V.
Min OSC (OSC) Load	Minimum load impedance for which distortion is guaranteed to be less than 5%.
Linearity Error	The degree to which the DC output of the demodulator/amplifier combination matches a change in the AC signal at the demodulator input. It is measured as the worst case nonlinearity from a straight line drawn between positive and negative fullscale end points.
Maximum Demodulator Input	The maximum signal that can be applied to the demodulator input without exceeding the specified linearity error.

## **APPLICATION INFORMATION**

OSC frequency = 
$$\frac{V_{REF} - 1.3V}{V_{REF} (R_T + 1.5k) C_T}$$

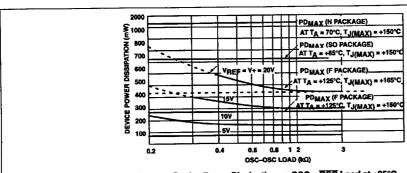


Figure 1. Device Power Dissipation vs OSC - OSC Load at +25°C

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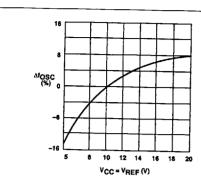


Figure 2. Oscillator Frequency Variation With Voltage (Normalized to  $V_{REF} = V_{CC} = 10V$ )  $T_A = +25^{\circ}C$ 

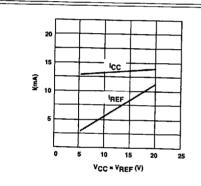


Figure 3.  $I_{REF}$  and  $I_{CC}$  vs Voltage ( $T_A = +25^{\circ}C$ )

